

EAST - [default.wsp:1]

File View Edit Tools Window Help

Drafts
Pending
Active
L1: (1585) (precharge or pre-charge) same different same
L2: (581) (precharge or pre-charge) with different with (potential or volt\$3 or charge or bias)
L3: (124) 2 with first with second
L4: (13) 3 with (data adj line)
Failed
Saved
Favorites

QB: USPAT;US-PGPUB;EPO;JPO
Default operator: OR
☒ Blends
☒ Highlight all hit terms initially

Type	L #	Hits	Search Text	DBs
BRS	L1	1585	(precharge or pre-charge) same different same (potential or volt\$3 or charge or bias)	USPAT; US-PGPUB; EPO; JPO
BRS	L2	581	(precharge or pre-charge) with different with (potential or volt\$3 or charge or bias)	USPAT; US-PGPUB; EPO; JPO
BRS	L3	124	2 with first with second	USPAT; US-PGPUB; EPO; JPO
BRS	L4	13	3 with (data adj line)	USPAT; US-PGPUB; EPO; JPO

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DBs: USPAT, US-PGPUB, EPO, JPO
Default operator: OR
3 with (data adj line)

DBS View SAR Item Image Text HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040032776 A1	20040219	9	Semiconductor memory device comprising circuit for precharging data line	365/203	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030090948 A1	20030515	36	Semiconductor device having memory cells coupled to read and write data lines	365/200	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20010048617 A1	20011206	36	Semiconductor integrated circuit	365/200	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6519195 B2	20030211	35	Semiconductor integrated circuit	365/203	365/187; 365/210
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6424571 B1	20020723	14	Sense amplifier with data line precharge through a self-bias circuit and a precharge circuit	365/185.21	327/51; 327/52;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6421264 B1	20020716	18	CAM Cell Circuit having decision circuit	365/49	365/154; 365/203;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6002624 A	19991214	10	Semiconductor memory device with input/output masking function without destruction of data bit	365/203	365/189.1
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5689468 A	19971118	69	Semiconductor memory device and method for driving the same	365/203	365/145; 365/149
9	<input type="checkbox"/>	<input type="checkbox"/>	US 5642314 A	19970624	28	Semiconductor integrated circuit	365/189.06	365/203; 365/205;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 5565796 A	19961015	31	Bus drive circuit, receiver circuit, and bus system	326/86	326/30; 326/31;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 5539279 A	19960723	34	Ferroelectric memory	365/145	365/149; 365/203
12	<input type="checkbox"/>	<input type="checkbox"/>	US 4893278 A	19900109	19	Semiconductor memory device including precharge/equalization circuitry for the complementary data lines	365/203	365/190
13	<input type="checkbox"/>	<input type="checkbox"/>	US 4888737 A	19891219	12	Semiconductor memory device	365/203	365/190

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